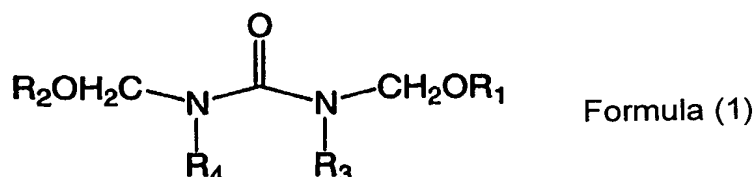


CLAIMS

1. A composition for forming anti-reflective coating characterized by containing a compound of formula (1)



wherein R_1 and R_2 are independently of each other hydrogen atom or an alkyl group, R_3 and R_4 are independently of each other hydrogen atom, methyl group, ethyl group, hydroxymethyl group or an alkoxyethyl group.

2. A composition for forming anti-reflective coating characterized by containing a resin produced from the compound of formula (1) according to claim 1.
3. The composition for forming anti-reflective coating according claim 2, wherein the resin is a condensation product produced from the compound of formula (1).
4. The composition for forming anti-reflective coating according to any one of claims 1 to 3, further containing a light absorbing compound and/or a light absorbing resin.
5. The composition for forming anti-reflective coating according to claim 4, wherein the light absorbing compound is at least one compound selected from naphthalene compounds and anthracene compounds.
6. The composition for forming anti-reflective coating according to claim 4, wherein the light absorbing compound is at least one compound selected from triazine compounds and triazine trione compounds.
7. The composition for forming anti-reflective coating according to claim 4,

wherein the light absorbing resin is a resin having in the structure at least one aromatic ring structure selected from benzene ring, naphthalene ring and anthracene ring.

8. The composition for forming anti-reflective coating according to any one of claims 1 to 3, further containing a resin having at least one crosslink-forming substituent selected from hydroxy group, carboxy group, amino group and thiol group.

9. The composition for forming anti-reflective coating according to any one of claims 1 to 3, further containing an acid and/or acid generator.

10. A method of forming an anti-reflective coating for use in a manufacture of a semiconductor device, characterized by comprising the steps of: coating the composition for forming anti-reflective coating according to any one of claims 1 to 3 on a substrate, and baking it.

11. A process for manufacturing a semiconductor device, characterized by comprising the steps of:
coating the composition for forming anti-reflective coating according to any one of claims 1 to 3 on a substrate and baking it to form an anti-reflective coating;
forming a photoresist on the anti-reflective coating;
exposing the substrate covered with the anti-reflective coating and the photoresist with a light;
developing it;
transferring an image on the substrate by etching to form an integrated circuit device.